

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (currently amended) A radiation-emitting semiconductor component having a layer structure, comprising:
  - an n-doped cladding layer (18),
  - a p-doped cladding layer (20),
  - an active layer (14) based on InGaAlP arranged between the n-doped cladding layer (18) and the p-doped cladding layer (20), and
  - a diffusion stop layer (16) arranged between the active layer (14) and the p-doped cladding layer (20), wherein  
the diffusion stop layer (16) has a strained superlattice and is highly n-doped.
2. (original) The radiation-emitting semiconductor component as claimed in claim 1, wherein  
the diffusion stop layer (16) has a superlattice which is alternately tensile/compressively strained.
3. (original) The radiation-emitting semiconductor component as claimed in claim 2, wherein the superlattice of the diffusion stop layer (16) has N periods of tensile-strained  $In_x(Ga_yAl_{1-y})_{1-x}P$  layers (16a), where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ , and compressively strained  $In_x(Ga_yAl_{1-y})_{1-x}P$  layers (16b), where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ .

$_{1-y}^{1-x}$ P layers (16b), where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ , N lying between 2 and 40, preferably between 5 and 20, particularly preferably between 8 and 15.

4. (original) The radiation-emitting semiconductor component as claimed in claim 3,  
wherein

the superlattice of the diffusion stop layer (16) consists of InAlP layers.

5. (original) The radiation-emitting semiconductor component as claimed in claim 1,  
wherein

the strain lies in the range of 0.1% to 5%, preferably in the range of 0.5% to 2%, particularly preferably in the range of 0.7% to 1%.

6. (original) The radiation-emitting semiconductor component as claimed in claim 1,  
wherein

the p-doped cladding layer (20) is p-doped with magnesium.

7. (canceled)

8. (currently amended) The radiation-emitting semiconductor component as  
claimed in claim [[7]] 1, wherein

the diffusion stop layer (16) is n-doped with tellurium.

9. (currently amended) The radiation-emitting semiconductor component as claimed in claim [[7]] 1, wherein the n-type dopant concentration lies above  $0.5 \times 10^{18} \text{ cm}^{-3}$ , in particular between them and including 0.75 and up to and including  $1.5 \times 10^{18} \text{ cm}^{-3}$ .

10. (Original) The radiation-emitting semiconductor component as claimed in claim 8, wherein

the n-type dopant concentration lies above  $0.5 \times 10^{18} \text{ cm}^{-3}$ , in particular between  $0.75 \times 10^{18} \text{ cm}^{-3}$  and  $1.5 \times 10^{18} \text{ cm}^{-3}$  (limits included).

11. (original) The radiation-emitting semiconductor component as claimed in claim 1, wherein

a transparent coupling-out layer (22), which preferably essentially consists of GaP, is arranged on the topmost cladding layer (20) of the layer structure.

12. (original) The radiation-emitting semiconductor component as claimed in claim 1, wherein

the active layer (14) comprises a p-n junction, a single quantum well structure or a multiple quantum well structure.

13. (original) The radiation-emitting semiconductor component as claimed in claim 2, wherein

the strain lies in the range of 0.1% to 5%, preferably in the range of 0.5% to 2%, particularly preferably in the range of 0.7% to 1%.

14. (original) The radiation-emitting semiconductor component as claimed in claim 3, wherein

the strain lies in the range of 0.1% to 5%, preferably in the range of 0.5% to 2%, particularly preferably in the range of 0.7% to 1%.

15. (original) The radiation-emitting semiconductor component as claimed in claim 4, wherein

the strain lies in the range of 0.1% to 5%, preferably in the range of 0.5% to 2%, particularly preferably in the range of 0.7% to 1%.

16. (original) The radiation-emitting semiconductor component as claimed in claim 3, wherein

a transparent coupling-out layer (22), which preferably essentially consists of GaP, is arranged on the topmost cladding layer (20) of the layer structure.

17. (original) The radiation-emitting semiconductor component as claimed in claim 4, wherein

a transparent coupling-out layer (22), which preferably essentially consists of GaP, is arranged on the topmost cladding layer (20) of the layer structure.

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18 - 20. (canceled)